

Physics of Materials and Nuclei - MidSem

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Semiconductor Physics

If the concentration ratio of conduction electrons and holes in a semiconductor with zero Hall coefficient is 16, estimate the ratio of mobilities of the conduction electron and holes.

1 point

- ☐ 1:4
- ☐ 4:1
- ☒ 1:16
- ☐ 1:2

Clear selection

Which of the following(s) is/are true for metals?

1 point

- ☒ conduction is due to drift current
- ☒ they obey Ohm's law
- ☒ they exhibit high thermal and electrical conductivities
- ☐ conduction is due to diffusion current



For a given semiconductor, the product of electron and hole concentration 1 point
changes with _____.

- ☐ pressure
- ☐ All of the above
- ☐ doping concentration
- ☒ temperature

Copper has a face-centered cubic lattice with interatomic spacing equal 2 points
to 0.254 nm. Estimate the Hall coefficient for copper by considering each
Cu atom contributes one valence electron.

- ☐ $+7.25 \times 10^{-11} \text{ m}^3/\text{C}$
- ☐ $-0.245 \times 10^{-9} \text{ m}^3/\text{C}$
- ☒ $-7.25 \times 10^{-11} \text{ m}^3/\text{C}$
- ☐ $+0.245 \times 10^{-9} \text{ m}^3/\text{C}$

Clear selection

At 400K, find the position of intrinsic Fermi level with respect to the mid of 1 point
the gap if the effective masses of electron and holes are 1.12 and 0.56
times of the rest mass of the electron, respectively.

- ☐ 17.9 meV below the mid gap
- ☒ 23.8 meV below the mid gap
- ☐ 17.9 meV above the mid gap
- ☐ 23.8 meV above the mid gap

Clear selection



Which of the following(s) is/are true about direct bandgap semiconductors?

1 point

- ☐ Silicon is a well known example of this type.
- ☒ an electron and a photon are involved in this process.
- ☒ are useful in the preparation of optical devices (LEDs and semiconductor lasers).
- ☐ law of mass action can not be applicable.

Which of the following statement(s) is/are true?

1 point

- ☐ Each donor atom contributes two free electrons to the semiconducting crystal lattice.
- ☒ Mobility of charge carriers equals its drift velocity divided by the applied electric field.
- ☒ A substitution impurity in donor and acceptor atoms does not cause any disturbances in the crystal lattice of semiconducting material.
- ☒ In an n-type semiconductor, the free electrons concentration approximately equals the density of donor atoms.

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